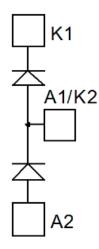
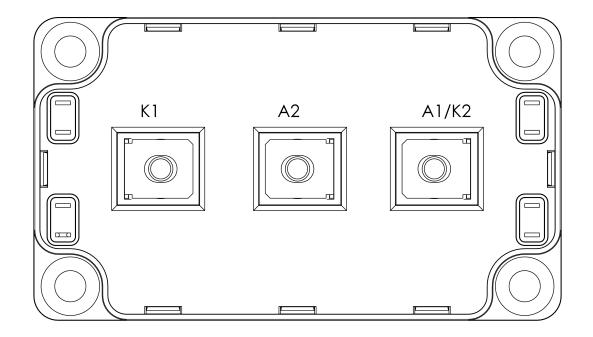


MSCDC600A120AG SiC Diode Phase Leg Power Module

1 Product Overview

This section provides the product overview for the MSCDC600A120AG device.





All ratings at T_j = 25 °C, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.



1.1 Features

The following are key features of the MSCDC600A120AG device:

- Silicon carbide (SiC) Schottky diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature-independent switching behavior
 - Positive temperature coefficient on VF
- Low stray inductance
- M5 power connectors
- High level of integration
- Aluminum nitride (AIN) substrate for improved thermal performance

1.2 Benefits

The following are benefits of the MSCDC600A120AG device:

- Outstanding performance at high-frequency operation
- Low noise switching
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- RoHS compliant

1.3 Applications

The MSCDC600A120AG device is designed for the following applications:

- Uninterruptible power supply (UPS)
- Induction heating
- Welding equipment
- High speed rectifiers



2 Electrical Specifications

This section provides the electrical specifications for the MSCDC600A120AG device.

2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings per diode for the MSCDC600A120AG device.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit
Vrrm	Repetitive peak reverse voltage		1200	V
lf	DC forward current	Tc = 85 °C	600*	А

* Specification of SiC device, but output current must be limited due to size of power connectors.

The following table shows the thermal and package characteristics of the MSCDC600A120AG.

Table 2 • Thermal and Package Characteristics

Characteristic			Min	Max	Unit
RMS isolation voltage, any terminal to case t =1 minute, 50 Hz/60 Hz					V
Operating junction temperature range			-40	175	°C
Recommended junction temperature under switching conditions			-40	TJmax-25	
Storage temperature range			-40	125	
Operating case temperature			-40	125	
Mounting torque	To heatsink	M6	3	5	N.m
	For terminals	M5	2	3.5	
Package weight				300	g
	RMS isolation voltage, any terminal to case t =1 Operating junction temperature range Recommended junction temperature under swi Storage temperature range Operating case temperature Mounting torque	RMS isolation voltage, any terminal to case t =1 minute, 50 Hz/60 H Operating junction temperature range Recommended junction temperature under switching conditions Storage temperature range Operating case temperature Mounting torque To heatsink For terminals	RMS isolation voltage, any terminal to case t =1 minute, 50 Hz/60 Hz Operating junction temperature range Recommended junction temperature under switching conditions Storage temperature range Operating case temperature Mounting torque To heatsink M6 For terminals M5	RMS isolation voltage, any terminal to case t =1 minute, 50 Hz/60 Hz 4000 Operating junction temperature range -40 Recommended junction temperature under switching conditions -40 Storage temperature range -40 Operating case temperature -40 Mounting torque To heatsink M6 For terminals M5 2	RMS isolation voltage, any terminal to case t =1 minute, 50 Hz/60 Hz 4000 Operating junction temperature range -40 175 Recommended junction temperature under switching conditions -40 T_jmax-25 Storage temperature range -40 125 Operating case temperature -40 125 Mounting torque To heatsink M6 3 5 For terminals M5 2 3.5

2.2 Electrical Performance

The following table shows the electrical characteristics per diode of the MSCDC600A120AG.

Table 3 • Electrical Characteristics Per Diode

Symbol	Characteristic Diode forward voltage	Test Conditions	Test Conditions		Тур	Max	Unit
VF		IF = 600 A	T _j = 25 °C		1.5	1.8	V
			T _j = 175 °C		2.1		_
Irm	Reverse leakage current	V _R = 1200 V	T _j = 25 °C		0.18	2.4	mA
			T _j = 175 °C		3		_
Qc	Total capacitive charge	V _R = 600 V			2688		nC
С	Total capacitance	f = 1 MHz, V _R = 400 V			2952		pF
		f = 1 MHz, V _R = 8	800 V		2184		_
RthJC	Junction-to-case thermal resist	ance				0.06	°C/W



2.3 Performance Curves

This section shows the typical performance curves for the MSCDC600A120AG device.

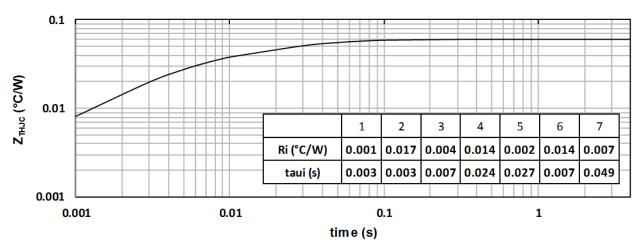


Figure 1 • Maximum Transient Thermal Impedance



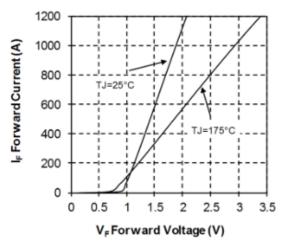
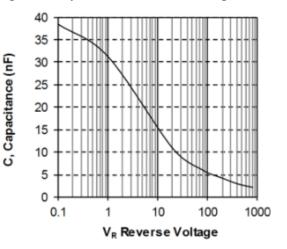


Figure 3 • Capacitance vs. Reverse Voltage





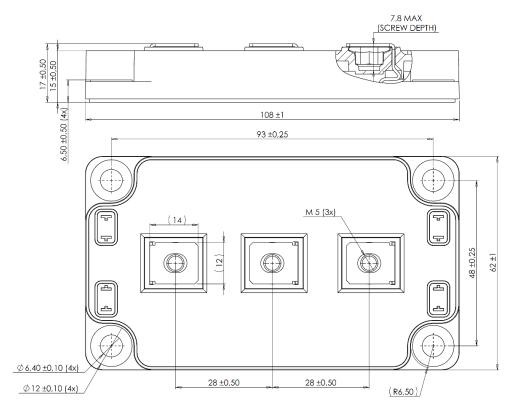
3 Package Specifications

This section shows the package specifications for the MSCDC600A120AG device.

3.1 Package Outline Drawing

The following drawing shows the package outline of the MSCDC600A120AG device. The dimensions in the following figure are in millimeters.

Figure 4 • Package Outline Drawing







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